

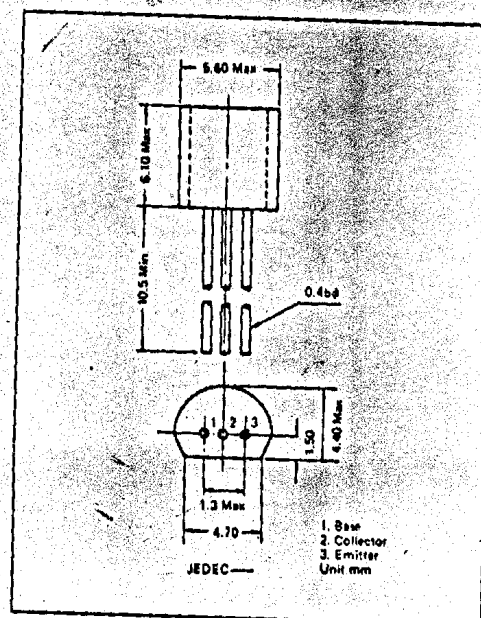
2SC1363, 1364

Silicon NPN APM Transistor

- 汎用増幅, 200mA, 320mW
- Complementary to 2SC1363: 2SA677
2SC1364: 2SA678
- Family 2SC1633, 2SC1634

絶対最大定格 Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Characteristics	Symbol	2SC1363	2SC1364
Collector-to-Base Voltage	V_{CB0}	25V	50V
Collector-to-Emitter Voltage	V_{CE0}	25V	50V
Emitter-to-Base Voltage	V_{EB0}	6V	
Collector Current	I_C	200 mA	
Base Current	I_B	50 mA	
Collector Power Dissipation	P_G	320 mW	
Junction Temperature	T_J	120°C	
Storage Temperature	T_{stg}	-30~+150°C	



電気的特性 Electrical Characteristics $T_a = 25^\circ\text{C}$

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = 25\text{V}, I_E = 0$			0.2	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB} = 6\text{V}, I_C = 0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 1\text{mA}$	82		690	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 10\text{mA}$		0.10	0.30	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$			0.82	1.20	V
Small Signal Current Gain	$ h_{fe} $	$V_{CE} = 6\text{V}, I_E = -2\text{mA}, f = 100\text{MHz}$		1.0	3.0	dB
Output Capacitance	C_{ob}	$V_{CB} = 6\text{V}, I_E = 0, f = 1\text{MHz}$		4.5	7.0	pF
Collector-to-Base Time Constant	$C_c \cdot r_{bb'}$	$V_{CB} = 6\text{V}, I_E = -2\text{mA}, f = 1.59\text{MHz}$		300	600	ps

規格細分 Classifications

Rank	$h_{FE} (I_C = 1\text{mA}, V_{CE} = 3\text{V})$
5	82-175
6	129-276
7	204-442
7	326-609